MA743

Silicon epitaxial planer type

■ Features

- MA704A and MA721 chip with two elements incorporated
- Fast reverse recovery period t_{rr}
- Auto mounting possible

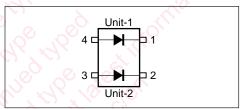
■ Absolute Maximum Ratings (Ta= 25°C)

Unit-1(MA704A)

Parameter	Symbol	Rating	Unit	
Reverse voltage (DC)	V_R	30	V	
Peak forward current	I _{FM}	150	mA	
Forward current (DC)	I_{F}	30	mA	
Junction temperature	T_j	125	°C	
Storage temperature	T_{stg}	- 55 to +125	°C	

Unit: mm $\frac{2.8 + 0.2}{0.65 \pm 0.15}$ $\frac{1.5 + 0.28}{0.00}$ $\frac{1.5$

■ Internal Connection



Unit-2(MA721)

Parameter	Symbol	Rating	Unit	
Reverse voltage (DC)	V_R	30	V	
Non-repetitive peak forward current	I _{FSM}	Q 1	A	
Peak forward current	I_{FM}	300	mA	
Average forward current	I _{F(AV)}	200	mA	
Junction temperature	Tj	150	°C	
Storage temperature	T _{stg}	- 55 to +150	°C	

Note 1. 50Hz sine wave, one-cycle wave, high value (non-repetitive)

2. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on charge of a human body and leakage from the equipment used.

■ Marking

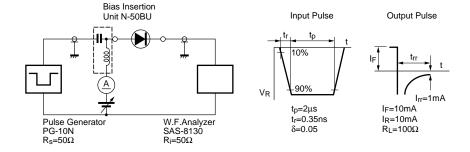


■ Electrical Characteristics (Ta= 25°C)

Unit-1(MA704A)

Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	$V_R = 30V$			300	μΑ
Forward voltage (DC)	V_{F1}	$I_F = 1 \text{mA}$			0.4	V
	V_{F2}	$I_F = 30 \text{mA}$			1.0	V
Terminal capacitance	C _t	V _R =1V, f=1MHz		1.5		pF
Reverse recovery time	. *	$I_F = I_R = 10 \text{mA}$		1.0		
	t _{rr} *	$I_{rr}=1$ mA, $R_L=100\Omega$				ns
Detection efficiency		$V_{in}=3V_{(peak)}, f=30MHz$		65		%
	η	$R_L=3.9k\Omega$, $C_L=10pF$				70

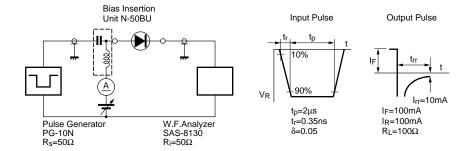
- Note 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on charge of a human body and leakage from the equipment used.
 - 2. Rated input/output frequency: 2000MHz
 - 3. * t_{rr} measuring circuit



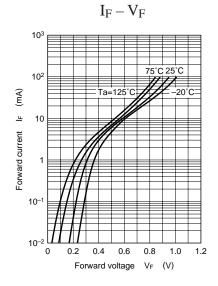
Unit-2(MA721)

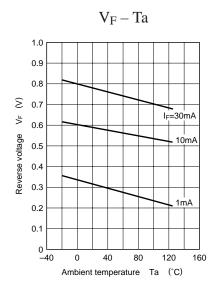
Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I _R	$V_R = 30V$			50	μΑ
Forward voltage (DC)	$V_{\rm F}$	$I_F = 200 \text{mA}$			0.55	V
Terminal capacitance	Ct	$V_R = 0V$, $f=1MHz$		30		pF
Reverse recovery time t_{rr}^*	4 *	$I_F = I_R = 100 \text{mA}$		3.0		ns
	ι _{rr}	$I_{rr}=10mA, R_L=100\Omega$				

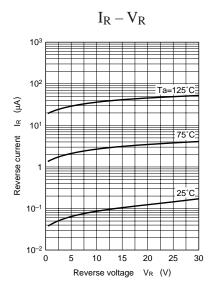
- Note 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on charge of a human body and leakage from the equipment used.
 - 2. Rated input/output frequency: 1000MHz
 - 3. * t_{rr} measuring circuit

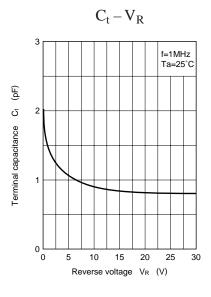


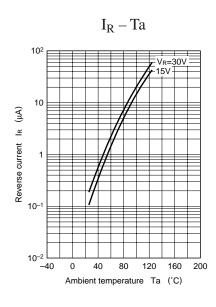
Characteristics chart of Unit-1 (MA704A)



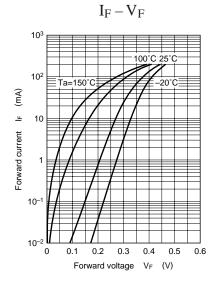


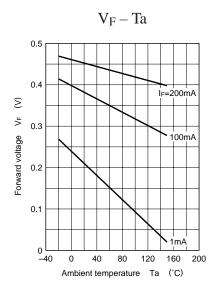


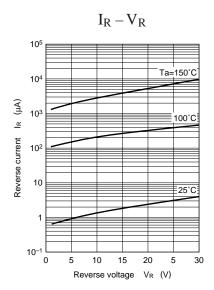


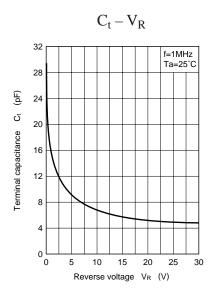


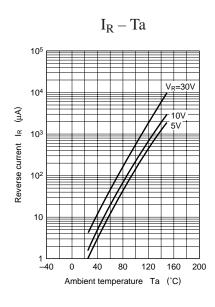
Characteristics chart of Unit-2 (MA721)











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